



AF 12814  
# 12  
2/15/03  
2003  
RECEIVED  
TECHNOLOGY CENTER 2800  
FEB - 3 2003

Docket No.: 8733.132.20-US  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Joon-Young Yang

Application No.: 09/875,197

Group Art Unit: 2814

Filed: June 7, 2001

Examiner: S. Rao

For: **METHOD OF FABRICATING A THIN FILM  
TRANSISTOR**

**AMENDMENT UNDER 37 CFR 1.116**

**Box AF**

Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 6, 2002, finally rejecting claims 21-34, 39 and 40, please amend the above-identified U.S. patent application as follows:

**In the Claims**

Please **CANCEL** Claims 21-34, 39 and 40 without prejudice.

Please **ADD** the following new claims:

41. (New) A method of fabricating a thin film transistor, comprising:

forming a gate insulating layer on an active layer;

forming a gate on the gate insulating layer;

forming an excited region in an exposed portion of the active layer by implanting hydrogen ions to the active layer by using the gate as a mask; and